FORM PTO-1449 (modified) Client Ref. Atty. To: U.S. Department of Commerce Dkt. No. (PW FORM PAT-1449) Patent and Trademark Office 308101 P-1810.000-US INFORMATION DISCLOSURE STATEMENT Applicant: **DUINEVELD** et al. BY APPLICANT Appln. No. 10/773,461 Filing Date: February 9, 2004 Page 1 of Examiner: Unknown Gulferer Group Art Unit: 2854-7851 Date: November 2, 2004 US PATENTIDOCUMENTS) HIGHER SELECTION OF THE SELECTION OF Examiners Document Filing Date Date Name Class Sub Class initials\* Number MMYYYY (Family Name of First Inventor) (if appropriate) U.-AR 3,573,975 04/1971 DHAKA et al. 117 212 03/1972 STEVENS BR 3,648,587 95 44 08/1982 TABARELLI et al. 430 311 CR 4,346,164 355 125 DR 4,390,273 06/1983 LOEBACH et al. 08/1983 AKEYAMA et al. 430 326 ER 4,396,705 355 FR 4,480,910 11/1984 TAKANASHI et al. 30 GR 4,509,852 04/1985 TABARELLI et al. 355 30 355 HR 5,040,020 08/1991 RAUSCHENBACH et al. 53 06/1992 359 664 IR 5,121,256 CORLE et al. JR 5,610,683 03/1997 TAKAHASHI 355 53 5,715,039 02/1998 FUKUDA et al. 355 53 KR 10/1998 SUWA 250 548 LR 5,825,043 05/1999 BATCHELDER 430 395 MR 5,900,354 NR 6,191,429 02/2001 SUWA 250 548 FOREIGN PATENT DOCUMENTS - LE STATE LE Document Country Inventor Name Date Available MMYYYY Number Enclosed No Enclosed No OR WO 99/49504 FUKAMI et al. Х 09/1999 PCT X X PR EP 0023231 02/1981 EUROPE TABARELLI et al. Х X QR EP 0418427 03/1991 EUROPE MIYAKE EUROPE MURAKAMI et al. Х Х RR EP 1039511 09/2000 HESSE et al. Х DD 224448 07/1985 GERMANY SR X KUCH TR DD 242880 02/1987 GERMANY **FRANCE** LETELLIER Х UR FR 2474708 07/1981 JP 62-065326 03/1987 JAPAN MORIUCHI X VR X NAKAZAWA JP 62-121417 06/1987 JAPAN

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